WHAT IS CLAIMED IS:

1. A method for reducing mismatch comprising:

determining a numerical first density of conductive structures within an active device in a high density region of a semiconductor substrate and a second density in a low density region of the semiconductor substrate, the high density region being adjacent the low density region; and

raising the second density in the low density region by adding dummy material in the low density region.

2. The method of claim 1, wherein the first density is an active area density.

3. The method of claim 1, wherein the first density is a conductor density.

4. The method of claim 1, further comprising:

determining a first overall density of a first region, wherein the first region comprises the high density region and the low density region;

determining a second overall density of a second region of the semiconductor substrate; and

adjusting either the first overall density or the second overall density to reduce a density mismatch between the first region and the second region.

5. The method of claim 4, wherein the adjusting either the first overall density or the second overall density reduces the density mismatch between the first region and the second region to within 2.5 % of each other.

6. The method of claim 4, further comprising adding the dummy material to a third region outside of and adjacent to the first region, the adding the dummy material raising a third density of the third region to reduce the density

mismatch between the third region and the first region.

7. The method of claim 1, wherein the raising the second density reduces the density mismatch between the low density region and the high density region to within 2.5% of each other.

8. A method for reducing mismatch comprising:

calculating a first density in a first region of a semiconductor device and a second density in a second region of the semiconductor device, wherein the first density and the second density are densities of conductive structures of active devices; and

adjusting the first density and the second density to generate an adjusted first density and an adjusted second density, the adjusting comprising adding dummy material to the first region and the second region, the adjusting also reducing a first density mismatch between the first region and the second region.

9. The method of claim 8, wherein the adjusting the first density and the second density is continued until the first density mismatch is less than about 2.5%.

10. The method of claim 8, further comprising:

determining a first internal density in a high density region of the first region;

determining a second internal density in a low density region of the first region; and

adjusting the second internal density in the low density region until an internal density mismatch between the first internal density and the second internal density is less than about 2.5 %, the adjusting comprising adding the dummy material to the low density region.

11. The method of claim 8, wherein the first density is a conductor density.

12. The method of claim 8, wherein the first density is an active area density.

13. The method of claim 8, further comprising:

determining a third density in the first region and a fourth density in the second region of the semiconductor device; and

adjusting the third density and the fourth density by adding dummy material to the first region and the second region, the adjusting reducing a second density mismatch between the first region and the second region, wherein the first density is a conductor density and the third density is an active area density.

14. The method of claim 8, further comprising:

determining an average density from the adjusted first density and the adjusted second density; and

adjusting a third density in a third region to the average density, the third region being between the first region and the second region.

~~15. A semiconductor device comprising:~~

~~a first region on a semiconductor substrate, the first region having a first density and comprising a first functional region and a first dummy region; and~~

~~a second region on the semiconductor substrate, the second region having a second density and comprising a second functional region and a second dummy region, wherein the first density and the second density are within 2.5% of each other.~~

~~16. The semiconductor device of claim 15, wherein the first density is a conductor density.~~

~~17. The semiconductor device of claim 15, wherein the first density is an active area density.~~

~~18. The semiconductor device of claim 15, wherein the first functional region has a third density and the first dummy region has a fourth density, the third density being within 2.5% of the fourth density.~~

~~19. The semiconductor device of claim 15, wherein a third region has a third density that is equal to or between the first density and the second density, the third region being located between the first region and the second region.~~

~~20. The semiconductor device of claim 15, wherein the first region has a third density within 2.5% of a fourth density of the second region, the first region being a conductor density and the third density being an active area density.~~

15. A method for reducing mismatch comprising:

calculating a first numerical number that represents a first density of first conductive structures in a first region, wherein the first conductive structures are part of first active devices;

calculating a second numerical number that represents a second density of second conductive structures in a second region, wherein the second conductive structures are part of second active devices;

comparing the first numerical number to the second numerical number; and

adjusting the first density or the second density based at least in part on the comparing the first numerical number to the second numerical number.

16. The method of claim 15, wherein the first density of first conductive structures is an active area density.

17. The method of claim 15, wherein the first density of first conductive structures is a gate electrode density.

18. The method of claim 15, wherein the adjusting the first density or the second density is continued until the first density mismatch is less than about 2.5%.

19. The method of claim 15, further comprising:

calculating a third numerical number that represents a third density of conductive structures in the second region;

calculating a fourth numerical number that represents a fourth density of conductive structures in the second region; and

adjusting the third density and the fourth density by adding dummy material to the first region and the second region, the adjusting reducing a density mismatch between the first region and the second region, wherein the first density is a gate electrode density and the third density is an active area density.

20. The method of claim 15, further comprising:

determining an average density after the adjusting the first density or the second density; and

adjusting a third density in a third region to the average density, the third region being between the first region and the second region.